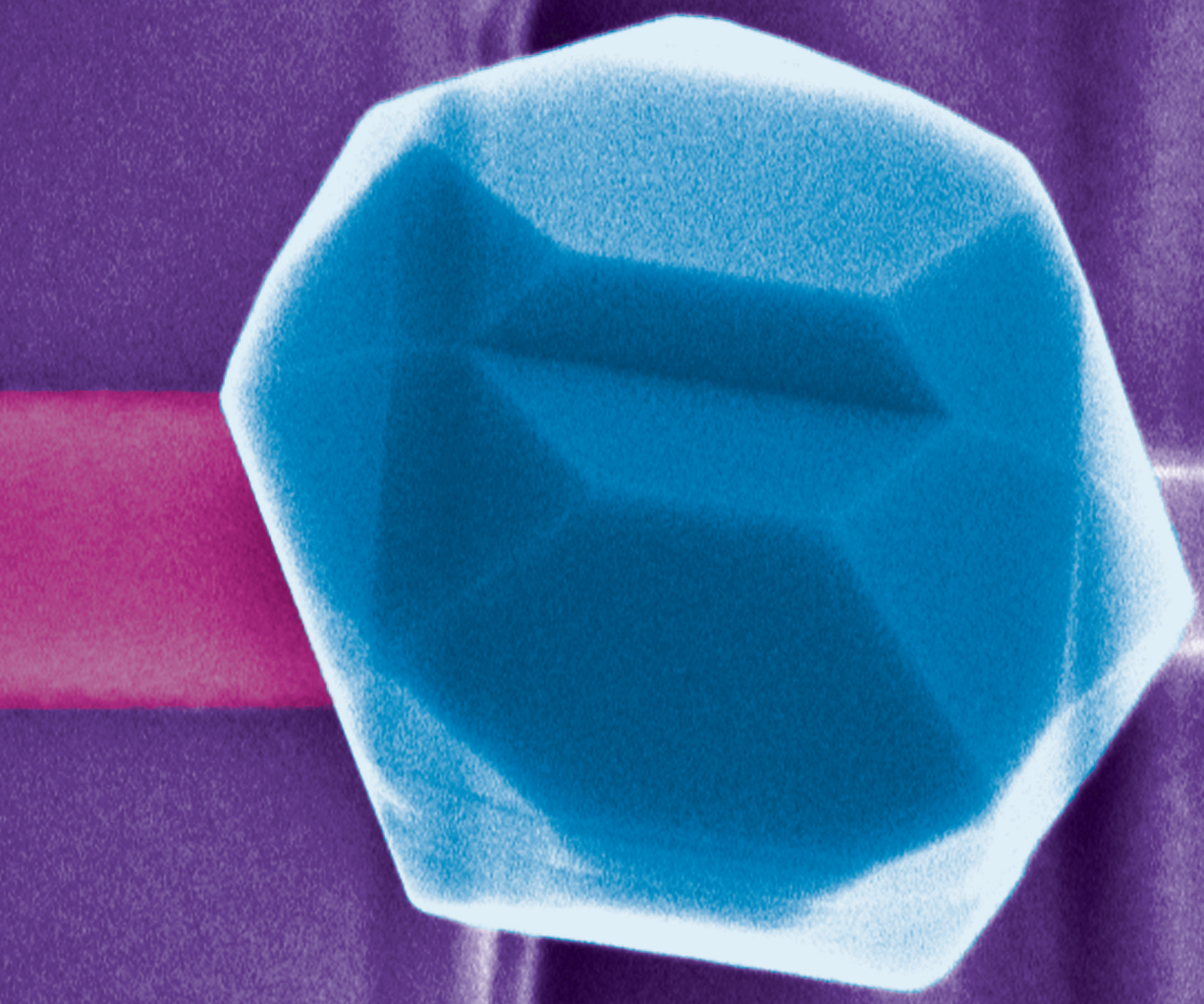
ADVANCED FUNCTIONAL MATERIALS



CRYSTAL GROWTH

A method for the growth of high-quality single-crystal germanium on amorphous silicon by ultrahigh vacuum chemical vapor deposition at temperatures less than 450 °C is presented on page 1049 by Jurgen Michel and co-workers. The growths proceed through constrictive channels and emerge with improved properties compared to as-deposited germanium. The growth mechanism and its implications for design of the growth structure are described.

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